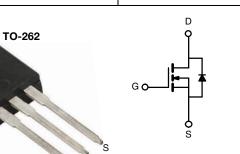


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Vishay Siliconix

Automotive N-Channel 60 V (D-S) 175 °C MOSFET

| PRODUCT SUMMARY | | | | | |
|---|---------|--|--|--|--|
| V _{DS} (V) | 60 | | | | |
| $R_{DS(on)}$ (Ω) at V_{GS} = 10 V | 0.00470 | | | | |
| $R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$ | 0.00600 | | | | |
| I _D (A) | 120 | | | | |
| Configuration | Single | | | | |
| Package | TO-262 | | | | |



N-Channel MOSFET

FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- AEC-Q101 qualified d
- 100 % R_a and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



| ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted) | | | | | |
|--|-------------------------------------|-----------------------------------|-------------|------|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Drain-Source Voltage | | V_{DS} | 60 | V | |
| Gate-Source Voltage | | V_{GS} | ± 20 | V | |
| Continuous Drain Current | T _C = 25 °C ^a | 1 | 120 | | |
| | T _C = 125 °C | l _D | 91 | | |
| Continuous Source Current (Diode Conduction) a | | I _S | 120 | Α | |
| Pulsed Drain Current ^b | | I _{DM} | 300 | | |
| Single Pulse Avalanche Current | L = 0.1 mH | I _{AS} | 80 | | |
| Single Pulse Avalanche Energy | L=0.1 IIII | E _{AS} | 320 | mJ | |
| Maximum Power Dissipation ^b | T _C = 25 °C | - P _D | 250 | W | |
| | T _C = 125 °C | | 83 | VV | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | -55 to +175 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | | |
|----------------------------|------------|-------------------|-------|--------|--|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | | |
| Junction-to-Ambient P | CB Mount c | R _{thJA} | 40 | °C /// | | |
| Junction-to-Case (Drain) | | R _{thJC} | 0.6 | °C/W | | |

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300 \, \mu s$, duty cycle $\leq 2 \, \%$.
- c. When mounted on 1" square PCB (FR4 material).
- d. Parametric verification ongoing.

Top View



Vishay Siliconix

| PARAMETER | SYMBOL | TEST CONDITIONS | | MIN. | TYP. | MAX. | UNIT |
|---|---------------------|--|---|------|---------|---------|------|
| Static | | 1 | | | | l | |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0, I _D = 250 μA | | 60 | - | - | V |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = | $V_{DS} = V_{GS}, I_D = 250 \mu A$ | | 2.0 | 2.5 | V |
| Gate-Source Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | | - | - | ± 100 | nA |
| | | $V_{GS} = 0 V$ | V _{DS} = 60 V | - | - | 1 | μA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{GS} = 0 V | V _{DS} = 60 V, T _J = 125 °C | - | - | 50 | |
| | | V _{GS} = 0 V | V _{DS} = 60 V, T _J = 175 °C | - | - | 500 | |
| On-State Drain Current ^a | I _{D(on)} | V _{GS} = 10 V | $V_{DS} \ge 5 V$ | 120 | - | - | Α |
| | | V _{GS} = 10 V | I _D = 30 A | - | 0.00378 | 0.00470 | Ω |
| Drain-Source On-State Resistance ^a | D | V _{GS} = 10 V | I _D = 30 A, T _J = 125 °C | - | - | 0.00801 | |
| Diain-Source On-State nesistance | R _{DS(on)} | V _{GS} = 10 V | I _D = 30 A, T _J = 175 °C | - | - | 0.00992 | |
| | | V _{GS} = 4.5 V | I _D = 20 A | - | 0.00481 | 0.00600 | |
| Forward Transconductance b | 9fs | V _{DS} = 15 V, I _D = 30 A | | - | 118 | - | S |
| Dynamic ^b | | | | | | | |
| Input Capacitance | C _{iss} | | V V _{DS} = 25 V, f = 1 MHz | - | 6705 | 8800 | pF |
| Output Capacitance | Coss | $V_{GS} = 0 V$ | | - | 904 | 1200 | |
| Reverse Transfer Capacitance | C _{rss} | | | - | 555 | 800 | |
| Total Gate Charge ^c | Qg | | | - | 148 | 230 | |
| Gate-Source Charge ^c | Q _{gs} | V _{GS} = 10 V | $V_{DS} = 30 \text{ V}, I_D = 85 \text{ A}$ | - | 21.4 | - | nC |
| Gate-Drain Charge ^c | Q _{gd} | | | - | 33.2 | - | |
| Gate Resistance | Rg | f = 1 MHz | | 0.45 | 0.99 | 1.5 | Ω |
| Turn-On Delay Time ^c | t _{d(on)} | $V_{DD}=30~V,~R_L=0.353~\Omega$ $I_D\cong85~A,~V_{GEN}=10~V,~R_g=1~\Omega$ | | - | 16 | 25 | |
| Rise Time ^c | t _r | | | - | 9 | 15 | ns |
| Turn-Off Delay Time ^c | t _{d(off)} | | | - | 46 | 75 | |
| Fall Time ^c | t _f | | | - | 12 | 20 | |
| Source-Drain Diode Ratings and Cha | racteristics b | | | | | | |
| Pulsed Current ^a | I _{SM} | | | - | - | 300 | Α |
| Forward Voltage | V_{SD} | I _F = 70 A, V _{GS} = 0 | | | 0.92 | 1.5 | V |

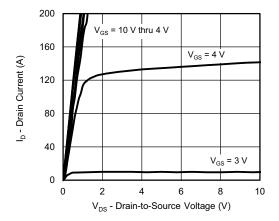
Notes

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

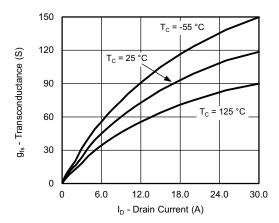
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



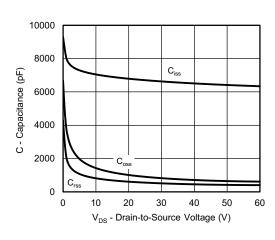
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Output Characteristics



Transconductance

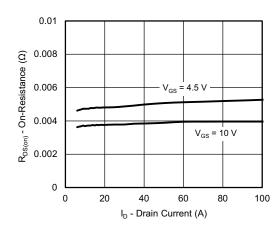


Capacitance

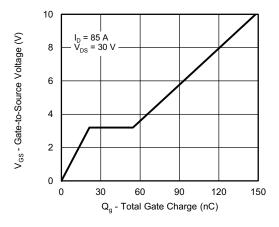
120

Transfer Characteristics

V_{GS} - Gate-to-Source Voltage (V)



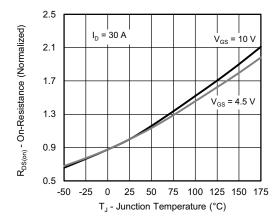
On-Resistance vs. Drain Current



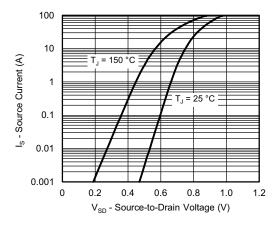
Gate Charge



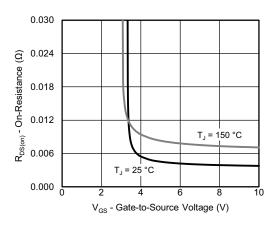
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



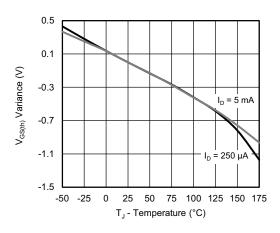
On-Resistance vs. Junction Temperature



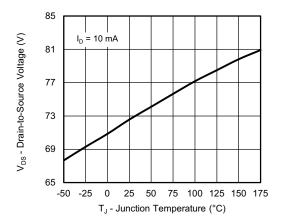
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



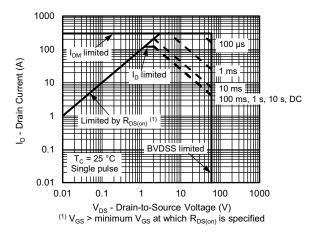
Threshold Voltage



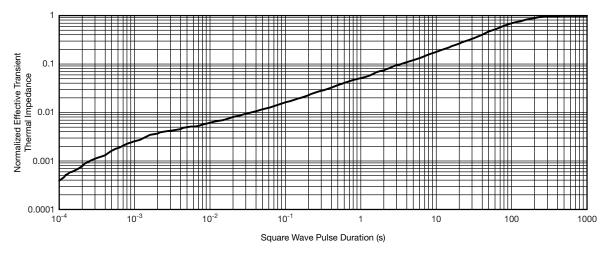
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



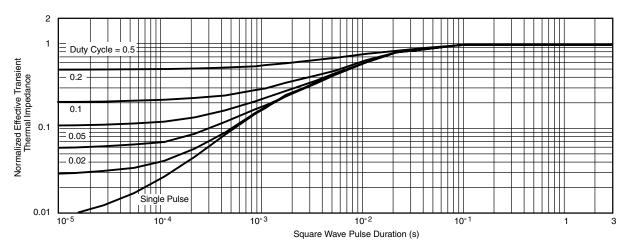
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

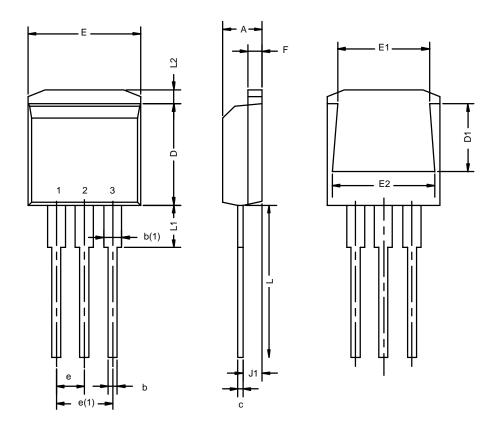
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg266962.



TO-262: 3-LEAD



| | MILLIM | ETERS* | INCHES | | |
|---|--------|--------|--------|-------|--|
| Dim | Min | Max | Min | Max | |
| Α | 4.32 | 4.70 | 0.170 | 0.185 | |
| b | 0.64 | 1.00 | 0.025 | 0.039 | |
| b(1) | 1.14 | 1.40 | 0.045 | 0.055 | |
| С | 0.36 | 0.50 | 0.014 | 0.020 | |
| D | 8.64 | 9.65 | 0.340 | 0.380 | |
| D1 | 5.59 | 6.10 | 0.220 | 0.240 | |
| е | 2.41 | 2.67 | 0.095 | 0.105 | |
| e(1) | 4.95 | 5.33 | 0.195 | 0.210 | |
| Е | 10.03 | 10.41 | 0.395 | 0.410 | |
| E1 | 7.87 | 8.64 | 0.310 | 0.340 | |
| E2 | 9.02 | 9.53 | 0.355 | 0.375 | |
| F | 1.14 | 1.40 | 0.045 | 0.055 | |
| J1 | 2.41 | 2.79 | 0.095 | 0.110 | |
| L | 13.08 | 14.22 | 0.515 | 0.560 | |
| L1 | - | 3.81 | - | 0.150 | |
| L2 | 1.02 | 1.40 | 0.040 | 0.055 | |
| ECN: T-02234—Rev. C, 14-Oct-02 DWG: 5855 | | | | | |

*Use millimeters as the primary measurement

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